

2. It is hereby certified:

- ☐ that each item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the Statement, or
- ☐ that no item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the person signing the certification after making reasonable inquiry, was known to any individual designated in § 1.56 (c) more than three months prior to the filing of the Statement.

3. ☒ Consideration of the following additional information (including any co-pending or abandoned U.S. applications, prior uses and/or sales, etc.) is requested:

Serial No. 10/616,086 entitled METHODS AND SYSTEMS FOR DETERMINING A PROPERTY OF AN INSULATING FILM

Serial No. 10/677,445 entitled METHODS FOR NON-CONTACTING DIFFERENTIAL VOLTAGE MEASUREMENTS

4. For each non-English language reference listed on the attached Form PTO-1449:

- ☐ reference is made to an English language translation submitted herewith, and/or
- ☐ reference is made to a foreign patent office search report (in the English language) submitted herewith, and/or
- ☐ reference is made to an English language translation of a foreign patent office search report submitted herewith, and/or
- ☐ reference is made to the concise explanation contained in the specification of the present application at page(s) _____, and/or
- ☐ reference is made to the concise explanation set forth below:

5. ☐ Applicant also offers the following comments for the Examiner's consideration:

6. ☐ Also enclosed is a copy of a foreign search report citing these references.

7. ☐ The listed documents were brought to the attention of the Applicant(s) after payment of the issue fee in the captioned case. The documents were cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement. Applicant(s) request this Information Disclosure Statement and attached Form PTO-1449 be placed in the file of the captioned application.

8. ☐ Applicant(s) requests that the Information Disclosure Statement and attached Form PTO-1449 and references, which are being filed before the grant of the patent and pursuant to 37 C.F.R. § 1.97(i), be placed in the file of the captioned application.

If any required fees are missing, the Commissioner is authorized to charge said fees to Conley Rose, P.C. Deposit Account No. 03-2769/5589-06800.

Respectfully submitted,



Ann Marie Mewherter
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Date: 3-19-04

Form PTO-1449 (modified) List of Patents and Publications For Applicant's Information Disclosure Statement (Use several sheets if necessary)	ATTY. DKT. NO. 5589-06800 APPLICANT: Shi et al. FILING DATE: October 31, 2003	SERIAL NO. 10/698,222 GROUP: Unknown
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U.S. PATENT DOCUMENTS

EXAM. INITIALS	REF. DES.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

EXAM. INITIALS	REF. DES.	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO
	A1	98/57358	1998-12-17	WO			

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	A2	Cosway et al., "Manufacturing Implementation of Corona Oxide Silicon (COS) Systems for Diffusion Furnace Contamination Monitoring," 1997 IEEE/SEMI Advanced Semiconductor Manufacturing Conference, pp. 98-102.
	A3	Miller, "A New Approach for Measuring Oxide Thickness," Semiconductor International, July 1995, pp. 147-148.
	A4	<u>Numerical Recipes in C, The Art of Scientific Computing, 2nd Ed.</u> , © Cambridge University Press 1988, 1992, p. 683.
	A5	Weinberg, "Tunneling of Electrons from Si into Thermally Grown SiO ₂ ," Solid-State Electronics, 1977, Vol. 20, pp. 11-18.
	A6	Verkuil, "Rapid Contactless Method for Measuring Fixed Oxide Charge Associated with Silicon Processing," IBM Technical Disclosure Bulletin, Vol. 24, No. 6, 1981, pp. 3048-3053.
	A7	"Contactless Photovoltage vs. Bias Method for Determining Flat-Band Voltage," IBM Technical Disclosure Bulletin, Vol. 32, Vol. 9A, 1990, pp. 14-17.
	A8	"Contactless Electrical Equivalent Oxide Thickness Measurement," IBM Technical Disclosure Bulletin, Vol. 29, No. 10, 1987, pp. 4622-4623.
	A9	Diebold et al., "Characterization and production metrology of thin transistor gate oxide films," Materials Science in Semiconductor Processing 2, 1999, pp. 103-147.
	A10	Comizzoli, "Uses of Corona Discharges in the Semiconductor Industry," J. Electrochem. Soc., 1987, pp. 424-429.
	A11	Weinzierl et al., "Non-Contact Corona-Based Process Control Measurements: Where We've Been, Where We're Headed," Electrochemical Society Proceedings, Vol. 99-16, pp. 342-350.
	A12	Verkuil et al., "A Contactless Alternative to MOS Charge Measurements by Means of a Corona-Oxide-Semiconductor (COS) Technique," Electrochem. Soc. Extended Abstracts, 1988, Vol. 88-1, No. 169, pp. 261-262.

EXAMINER:

DATE CONSIDERED:

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the patent owner.